CLMPTO

01/24/05

1. (Previously Presented) A method of forming multi-layers for manufacturing a thin

film transistor (TFT) using multiple process chambers, comprising:

forming a first layer of silicon dioxide for the thin film transistor on a glass substrate using a first non-chemical physical vapor deposition in a first process chamber;

transferring the substrate including the first layer to a second process chamber without breaking vacuum;

sequentially forming a second layer of amorphous silicon for the thin film transistor in the second process chamber using a second non-chemical physical vapor deposition on the first layer without breaking vacuum for fabricating the thin film transistor; and

forming additional layers on top of the second layer for completing formation of the thin film transistor.

2. (Previously Presented) The method of claim 1, wherein the physical vapor deposition for forming the first layer and the second layer comprises pulsed-DC or RF sputtering.

3. (Currently Amended) The method of claim 1, wherein the first layer is formed usi gas mixture of $Ar+O2_2$ using a $SiO2_2$ target P-doped with a resistivity of 1-50 Ohms-centimeters.

4. (Currently Amended) The method of claim 3, wherein the first layer, the second layer and the additional layers form the thin film transistor into a liquid crystal diode display(LCD).

CLAIMS 5-13 (CANCELLED)

14. (Original) The method of claim 1, wherein said forming a first layer is performed by sputtering using a first target comprising silicon dioxide.

15. (Original) The method of claim 1, wherein said forming a second layer is performed by sputtering using a target formed of a material selected from the group consisting of single crystalline silicon and polycrystalline silicon.

16. (Original) The method of claim 1, wherein the physical vapor deposition for forming the second layer comprises regular-DC, pulsed DC or RF sputtering.

CLAIMS 17– 40 (CANCELLED)